

Kihun Choe

List of Publications by Year in descending order

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16
papers

204
citations

1307594

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1199594

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16
times ranked

145
citing authors

#	ARTICLE	IF	CITATIONS
1	Direct comparison of ferroelectric properties in Hf _{0.5} Zr _{0.5} O ₂ between thermal and plasma-enhanced atomic layer deposition. Nanotechnology, 2020, 31, 505707.	2.6	45
2	Adjusting the Operating Voltage of an Nanoelectromechanical Relay Using Negative Capacitance. IEEE Transactions on Electron Devices, 2017, 64, 5270-5273.	3.0	25
3	Ferroelectric HfO ₂ -based synaptic devices: recent trends and prospects. Semiconductor Science and Technology, 2021, 36, 104001.	2.0	25
4	Variability Study of Ferroelectric Field-Effect Transistors Towards 7nm Technology Node. IEEE Journal of the Electron Devices Society, 2021, 9, 1131-1136.	2.1	16
5	Impact of Random Phase Distribution in Ferroelectric Transistors-Based 3-D NAND Architecture on In-Memory Computing. IEEE Transactions on Electron Devices, 2021, 68, 2543-2548.	3.0	15
6	3D AND-Type Ferroelectric Transistors for Compute-in-Memory and the Variability Analysis. IEEE Electron Device Letters, 2022, 43, 304-307.	3.9	15
7	Variability Analysis for Ferroelectric Field-Effect Transistors. , 2021, , .		10
8	Gate-induced drain leakage (GIDL) in MFMS and MFIS negative capacitance FinFETs. Current Applied Physics, 2020, 20, 1222-1225.	2.4	9
9	Ferroelectric-Gated Nanoelectromechanical Nonvolatile Memory Cell. IEEE Transactions on Electron Devices, 2019, 66, 407-412.	3.0	8
10	Experimental RF Characterization of Ferroelectric Hafnium Zirconium Oxide Material at GHz for Microwave Applications. , 2021, , .		8
11	Multigate Ferroelectric Transistor Design Toward 3-nm Technology Node. IEEE Transactions on Electron Devices, 2021, 68, 5908-5911.	3.0	7
12	Impact of negative capacitance on the energy-delay property of an electromechanical relay. Japanese Journal of Applied Physics, 2019, 58, 051003.	1.5	5
13	Impact of Random Phase Distribution in 3D Vertical NAND Architecture of Ferroelectric Transistors on In-Memory Computing. , 2020, , .		5
14	Compute-in-Memory: From Device Innovation to 3D System Integration. , 2021, , .		5
15	Theoretical study of ferroelectric-gated nanoelectromechanical diode nonvolatile memory cell. Solid-State Electronics, 2020, 163, 107662.	1.4	3
16	Energy-Delay Sensitivity Analysis of a Nanoelectromechanical Relay With the Negative Capacitance of a Ferroelectric Capacitor. IEEE Journal of the Electron Devices Society, 2020, 8, 365-372.	2.1	3